

Final datasheet

Short circuit rugged 1200 V TRENCHSTOP™ IGBT 7 technology

Features

- $V_{CE} = 1200\text{ V}$
- $I_C = 8\text{ A}$
- Low saturation voltage $V_{CEsat} = 2\text{ V}$ at $T_{vj} = 150^\circ\text{C}$
- Short circuit ruggedness $8\text{ }\mu\text{s}$
- Wide range of dv/dt controllability
- Complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>

Potential applications

- Industrial drives

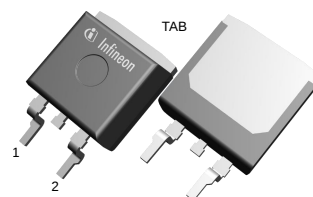
Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22
- Encapsulation for the application required

Description

Package pin definition:

- Pin 1 (G) - gate
- Pin 2 (E) - emitter
- TAB (C) - collector



Halogen-free



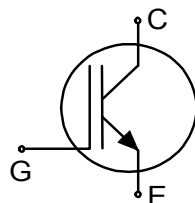
Lead-free



Green



RoHS



Type	Package	Marking
IGB08N120S7	PG-TO263-3-STD-C1.6	G08MS7



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1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			7		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	reflow soldering (MSL1 according to JEDEC J-STA-020)			260	°C
Thermal resistance, 6 cm ² Cu on PCB junction to ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			1.07	1.44	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25\text{ °C}$		1200	V
DC collector current, limited by T_{vjmax}	I_C		$T_c = 25\text{ °C}$	20 ¹⁾	A
			$T_c = 100\text{ °C}$	13	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			24	A
Turn-off safe operating area		$V_{CE} \leq 1200\text{ V}, T_{vj} \leq 150\text{ °C}$		24	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5\text{ }\mu\text{s}, D < 0.001$		±25	V
Short-circuit withstand time	t_{SC}	$V_{CC} \leq 600\text{ V}, V_{GE} = 15\text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}, T_{vj} = 150\text{ °C}$		8	μs
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	87	W
			$T_c = 100\text{ °C}$	35	

1) Limited by bondwire

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 8\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$		1.65	2	V
			$T_{vj} = 150\text{ °C}$		2		
Gate-emitter threshold voltage	V_{GETh}	$I_C = 0.16\text{ mA}$, $V_{CE} = V_{GE}$		5.15	5.7	6.45	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 1200\text{ V}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			20	μA
			$T_{vj} = 150\text{ °C}$		130		
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$				100	nA
Transconductance	g_{fs}	$I_C = 8\text{ A}$, $V_{CE} = 20\text{ V}$, $T_{vj} = 150\text{ °C}$			3.6		S
Short-circuit collector current	I_{SC}	$V_{CC} \leq 600\text{ V}$, $V_{GE} = 15\text{ V}$, $t_{SC} \leq 8\text{ }\mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 150\text{ °C}$			38		A
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			1.3		nF
Output capacitance	C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			24		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			17		pF
Gate charge	Q_G	$V_{CC} = 960\text{ V}$, $I_C = 8\text{ A}$, $V_{GE} = 15\text{ V}$			55		nC
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		15		ns
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		14		
Rise time (inductive load)	t_r	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		15		ns
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		18		
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		149		ns
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		225		
Fall time (inductive load)	t_f	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		131		ns
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		246		
Turn-on energy	E_{on}	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		0.46		mJ
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		0.67		
Turn-off energy	E_{off}	$V_{CC} = 600\text{ V}$, $V_{GE} = 0/15\text{ V}$, $R_{G(on)} = 20\text{ }\Omega$, $R_{G(off)} = 20\text{ }\Omega$	$T_{vj} = 25\text{ °C}$, $I_C = 8\text{ A}$		0.41		mJ
			$T_{vj} = 150\text{ °C}$, $I_C = 8\text{ A}$		0.73		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Total switching energy	E_{ts}	$V_{CC} = 600 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_{G(on)} = 20 \Omega$, $R_{G(off)} = 20 \Omega$	$T_{vj} = 25 \text{ °C}$, $I_C = 8 \text{ A}$		0.87		mJ
			$T_{vj} = 150 \text{ °C}$, $I_C = 8 \text{ A}$		1.4		
Operating junction temperature	T_{vj}			-40		150	°C

Note: For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Electrical Characteristic at $T_{vj} = 25 \text{ °C}$, unless otherwise specified.

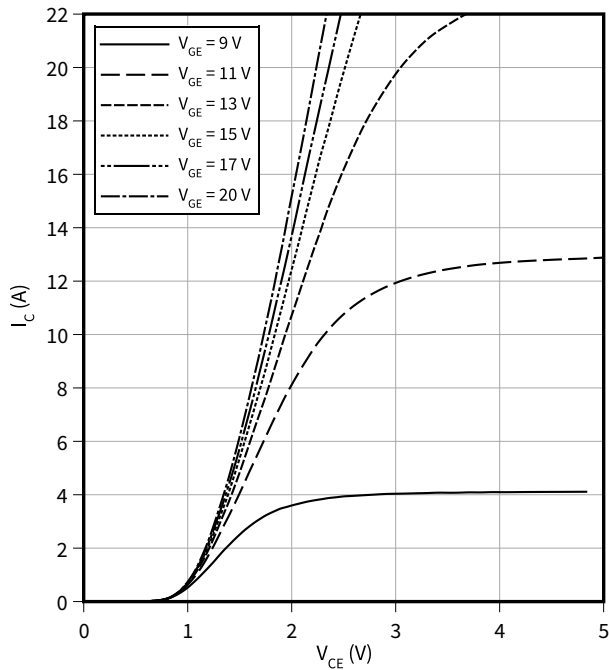
Dynamic test circuit, parasitic inductance $L_\sigma = 45 \text{ nH}$, parasitic capacitor $C_\sigma = 25 \text{ pF}$ from Fig. E. Energy losses include “tail” and diode (IKW08N120CS7) reverse recovery.

3 Characteristics diagrams

Typical output characteristic

$I_C = f(V_{CE})$

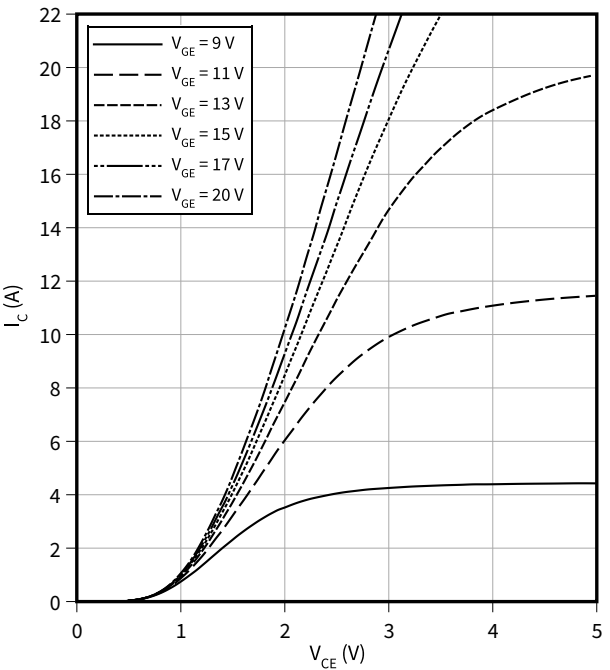
$T_{vj} = 25\text{ }^{\circ}\text{C}$



Typical output characteristic

$I_C = f(V_{CE})$

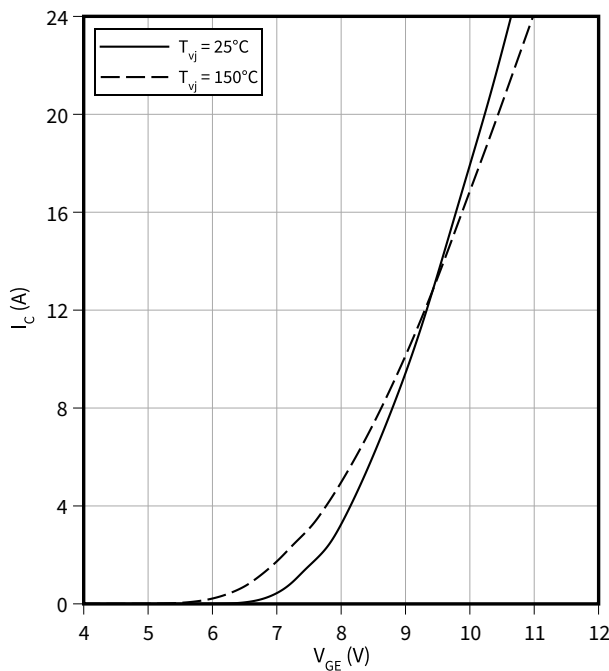
$T_{vj} = 150\text{ }^{\circ}\text{C}$



Typical transfer characteristic

$I_C = f(V_{GE})$

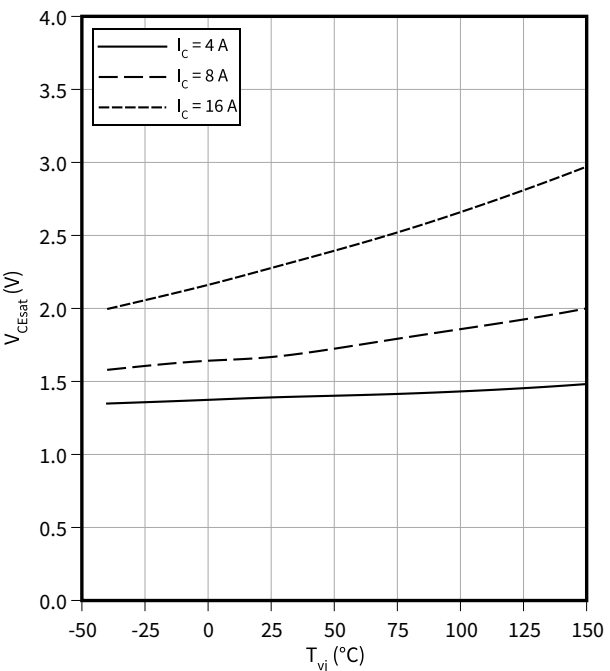
$V_{CE} = 20\text{ V}$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

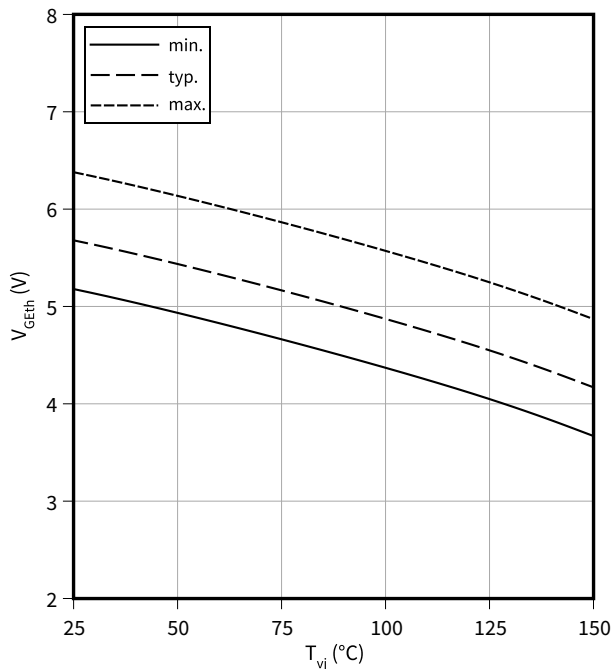
$V_{GE} = 15\text{ V}$



3 Characteristics diagrams

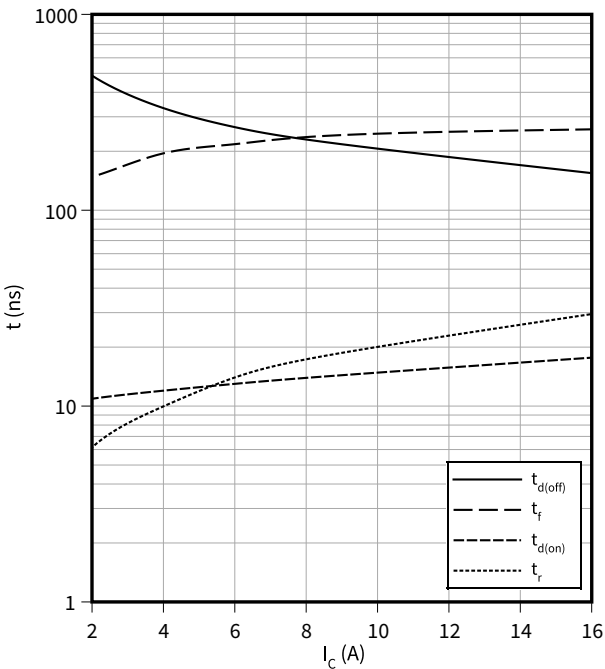
Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$
 $I_C = 0.16 \text{ mA}$



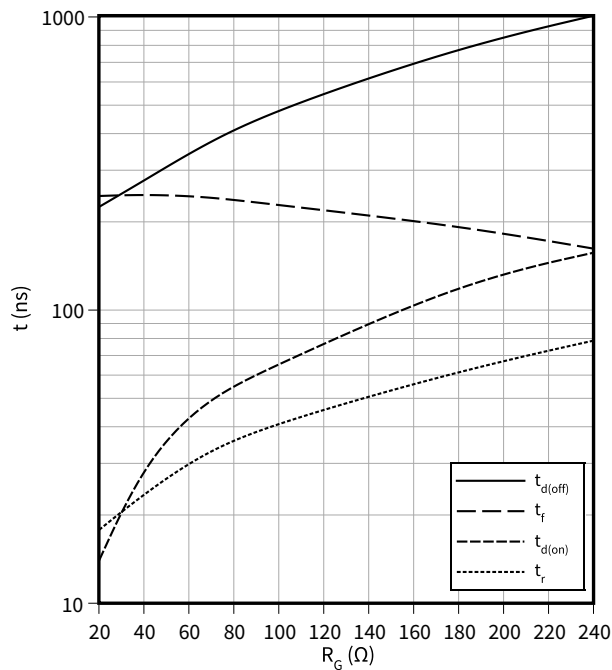
Typical switching times as a function of collector current

$t = f(I_C)$
 $V_{CC} = 600 \text{ V}, T_{vj} = 150 \text{ °C}, V_{GE} = 0/15 \text{ V}, R_G = 20 \text{ }\Omega$



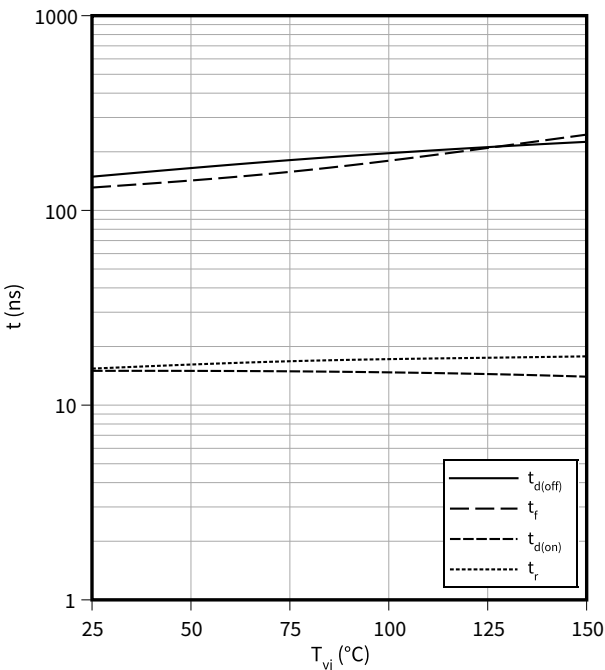
Typical switching times as a function of gate resistor

$t = f(R_G)$
 $I_C = 8 \text{ A}, V_{CC} = 600 \text{ V}, T_{vj} = 150 \text{ °C}, V_{GE} = 0/15 \text{ V}$



Typical switching times as a function of junction temperature

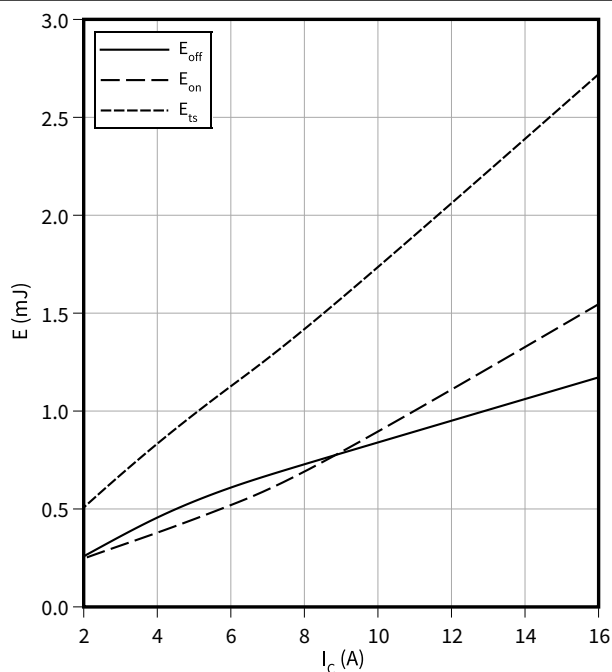
$t = f(T_{vj})$
 $I_C = 8 \text{ A}, V_{CC} = 600 \text{ V}, V_{GE} = 0/15 \text{ V}, R_G = 20 \text{ }\Omega$



Typical switching energy losses as a function of collector current

$$E = f(I_C)$$

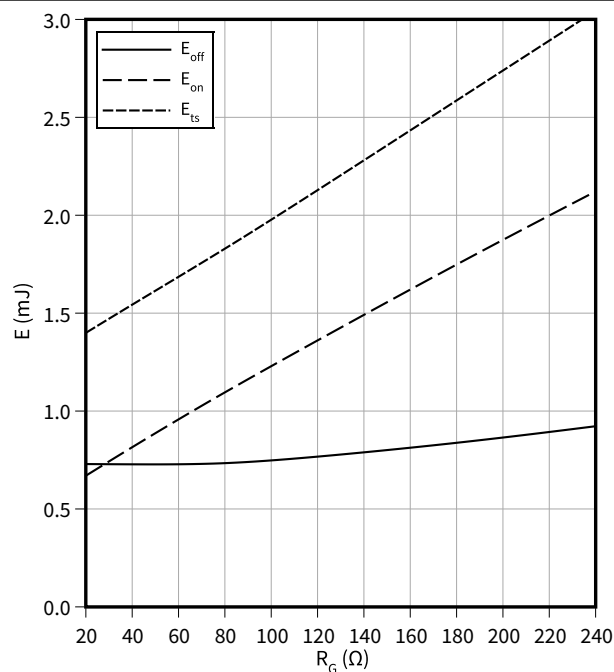
$V_{CC} = 600 \text{ V}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20 \text{ } \Omega$



Typical switching energy losses as a function of gate resistor

$$E = f(R_G)$$

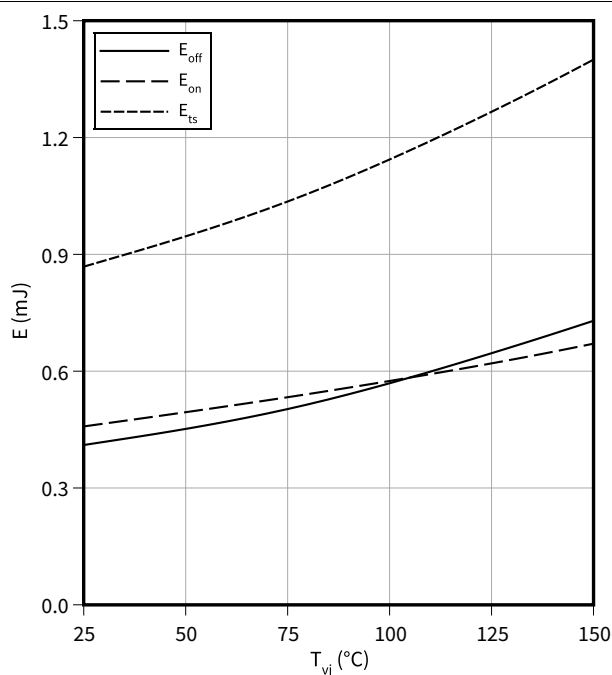
$I_C = 8 \text{ A}$, $V_{CC} = 600 \text{ V}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$, $V_{GE} = 0/15 \text{ V}$



Typical switching energy losses as a function of junction temperature

$$E = f(T_{vj})$$

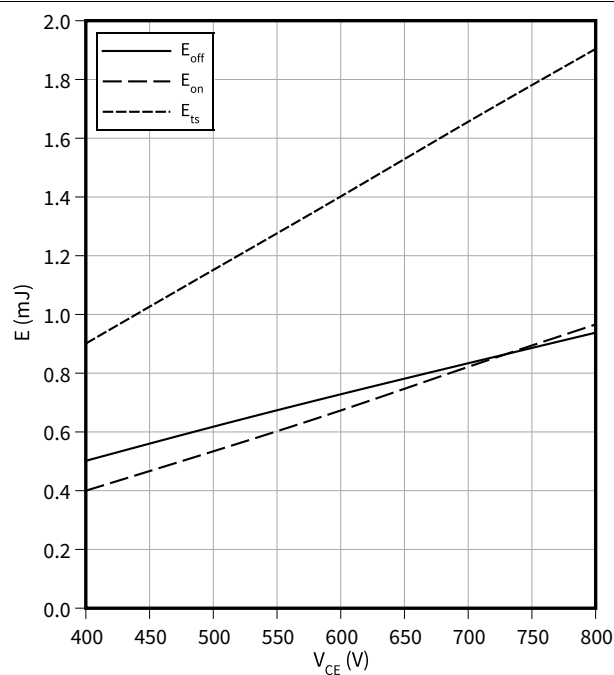
$I_C = 8 \text{ A}$, $V_{CC} = 600 \text{ V}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20 \text{ } \Omega$



Typical switching energy losses as a function of collector emitter voltage

$$E = f(V_{CE})$$

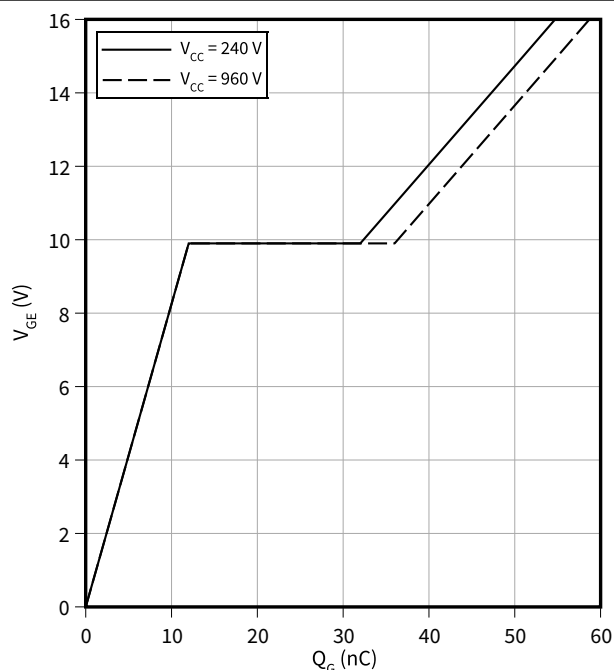
$I_C = 8 \text{ A}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$, $V_{GE} = 0/15 \text{ V}$, $R_G = 20 \text{ } \Omega$



3 Characteristics diagrams
Typical gate charge

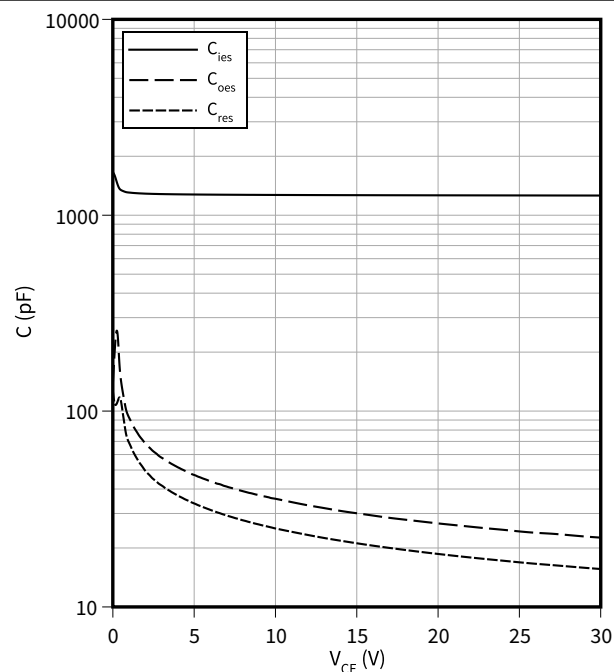
$$V_{GE} = f(Q_G)$$

$$I_C = 8 \text{ A}$$


Typical capacitance as a function of collector-emitter voltage

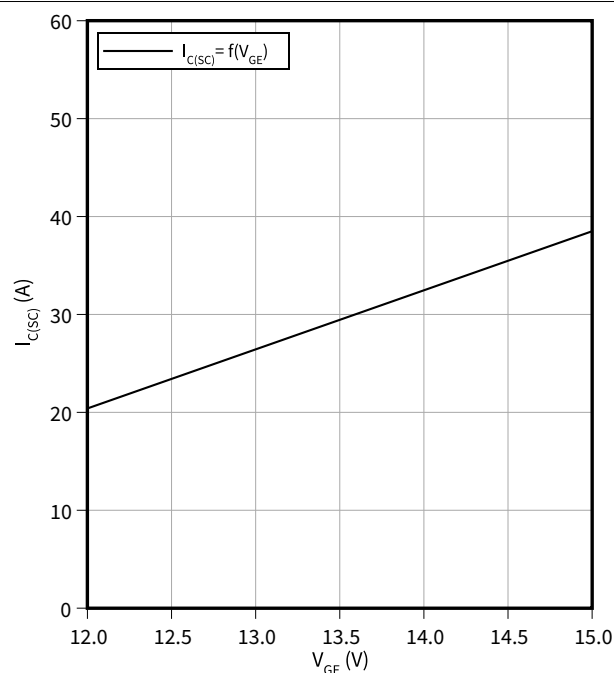
$$C = f(V_{CE})$$

$$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}$$


Typical short circuit collector current as a function of gate-emitter voltage

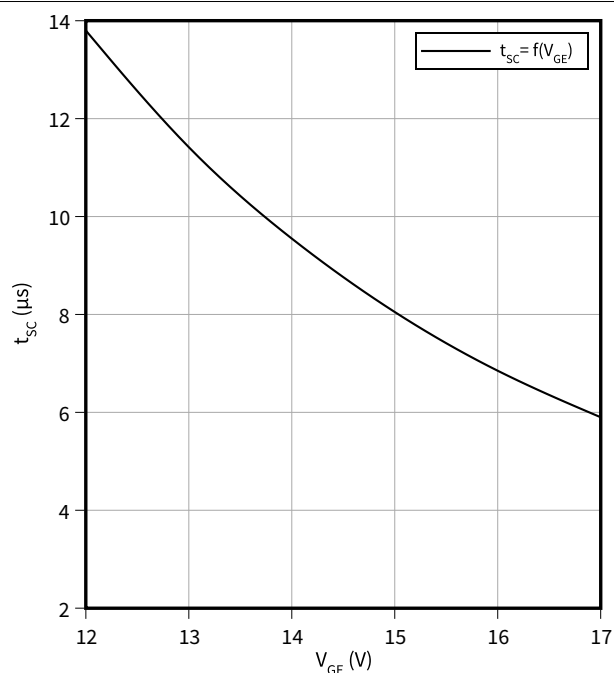
$$I_{C(SC)} = f(V_{GE})$$

$$T_{vj} = 150 \text{ }^\circ\text{C}, V_{CC} = 600 \text{ V}$$


Short circuit withstand time as a function of gate-emitter voltage

$$t_{SC} = f(V_{GE})$$

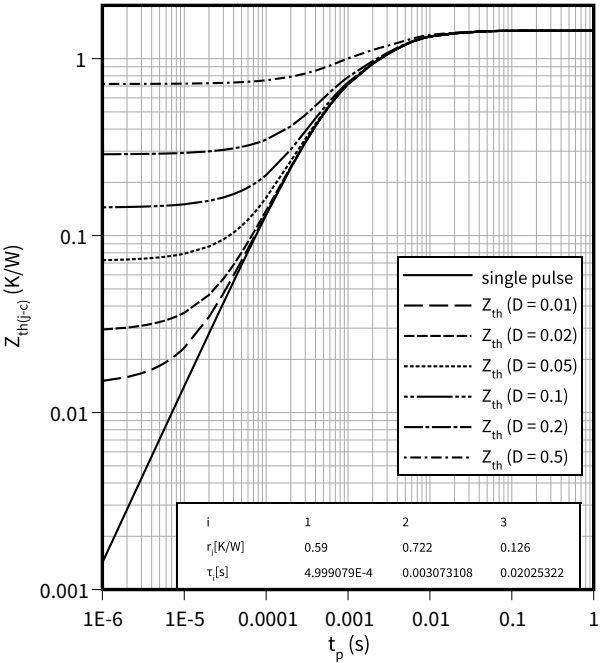
$$T_{vj} = 150 \text{ }^\circ\text{C}, V_{CC} = 600 \text{ V}$$



3 Characteristics diagrams

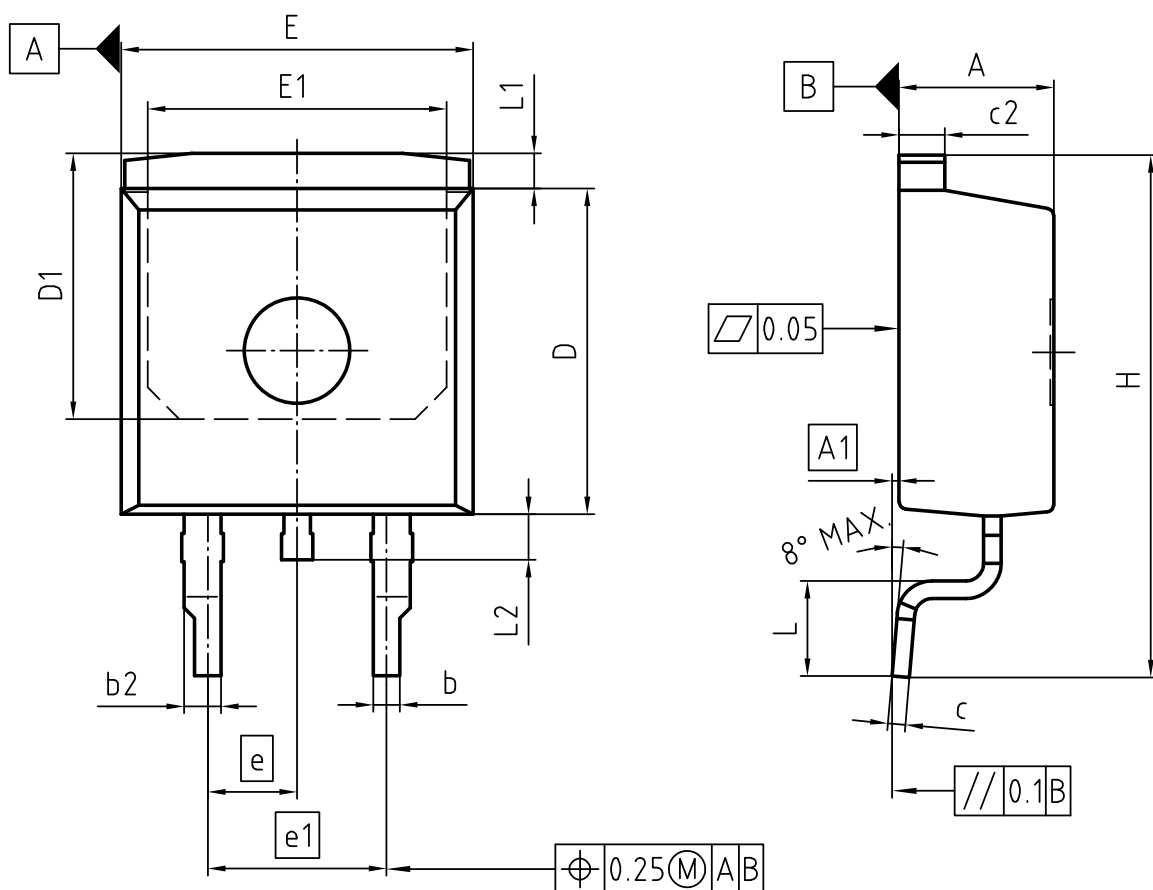
IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



4 Package outlines

PG-TO263-3-STD-C1.6



PACKAGE - GROUP NUMBER: PG-TO263-3-U01		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.30	4.50
A1	0.00	0.10
b	0.65	0.85
b2	0.95	1.15
c	0.40	0.60
c2	1.17	1.37
D	9.05	9.45
D1	7.45	7.65
E	9.80	10.20
E1	8.40	8.60
e	2.54	
e1	5.08	
N	2	
H	14.60	15.90
L	2.40	3.00
L1	0.70	1.30
L2	1.00	1.60

Figure 1

5 Testing conditions

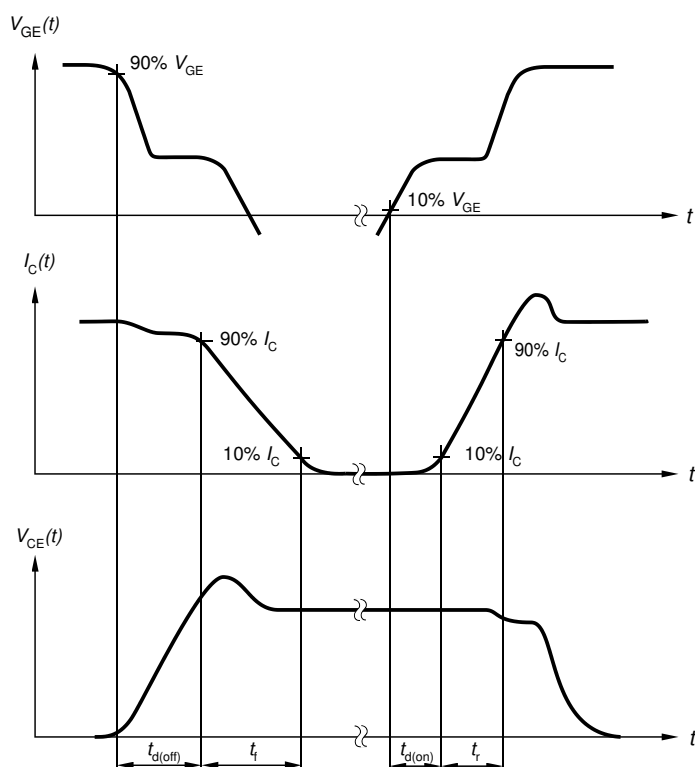


Figure A. Definition of switching times

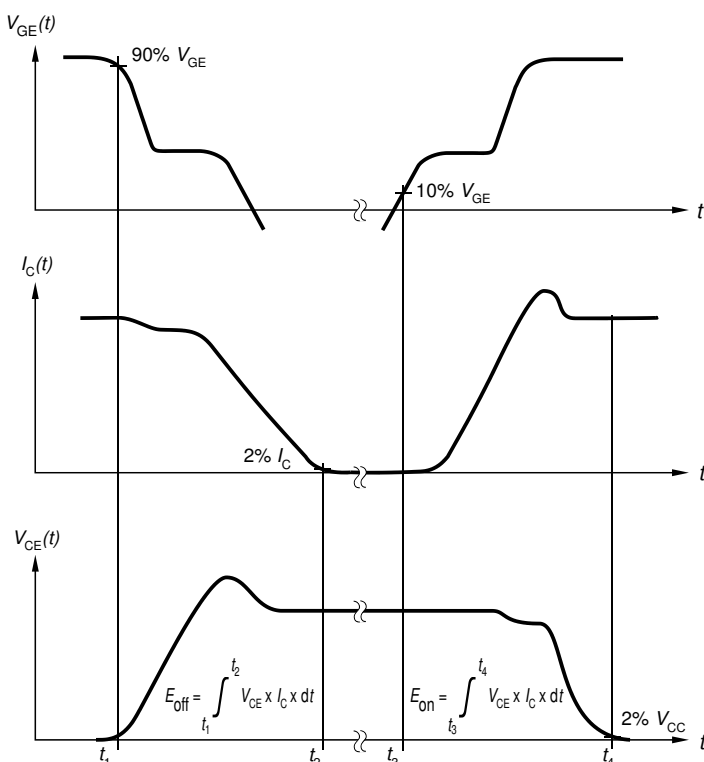


Figure B. Definition of switching losses

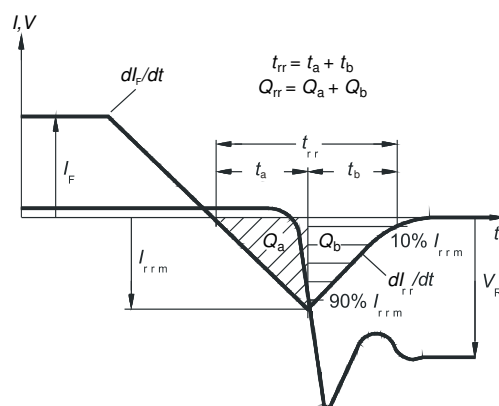


Figure C. Definition of diode switching characteristics

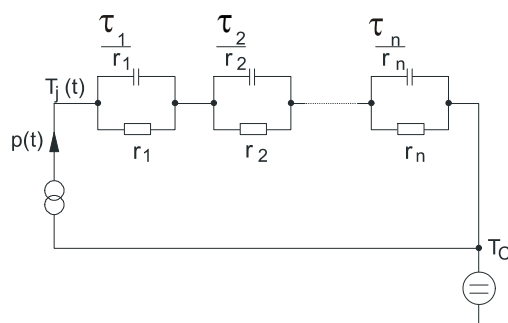


Figure D. Thermal equivalent circuit

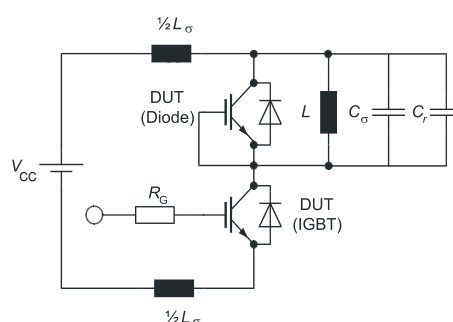


Figure E. **Dynamic test circuit**
 Parasitic inductance L_σ ,
 parasitic capacitor C_σ ,
 relief capacitor C_r ,
 (only for ZVT switching)



Revision history

Document revision	Date of release	Description of changes
1.00	2024-03-11	Final datasheet

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Edition 2024-03-11

Published by

Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-ABD971-001

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